

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1597	257/388,E21.199, E21.622.ccls. or 438/664. ccls.	US-PGPUB; USPAT	OR	ON	2008/05/20 11:23
L2	52	(gate and stack and (insulat\$3 or dielectric) and (Si or Ge) and metal and thick\$4 and (anneal \$3 or heat\$3) and reaction and ((work with function) or work \$function) and (mid \$gap))	US-PGPUB	OR	ON	2008/05/20 12:09
L3	0	(gate and stack and (insulat\$3 or dielectric) and (Si or Ge) and metal and thick\$4 and (anneal \$3 or heat\$3) and reaction and ((work with function) or work \$function) and (mid \$gap)).CLM.	US-PGPUB	OR	ON	2008/05/20 12:11
L4	3	(gate and stack and (insulat\$3 or dielectric) and (Si or Ge) and metal and thick\$4 and (anneal \$3 or heat\$3) and reaction and ((work with function) or work \$function)).CLM.	US-PGPUB	OR	ON	2008/05/20 12:12
L5	3	(gate and stack and (insulat\$3 or dielectric) and silicon and metal and thick\$4 and (anneal \$3 or heat\$3) and reaction and ((work with function) or work \$function)).CLM.	US-PGPUB	OR	ON	2008/05/20 12:13

L6	0	(gate and stack and (insulat\$3 or dielectric) and silicon and metal and thick\$4 and (anneal \$3 or heat\$3) and reaction and ((work with function) or work \$function) and (band with gap)).CLM.	US-PGPUB	OR	ON	2008/05/20 12:14
L7	0	(gate and stack and (insulat\$3 or dielectric) and silicon and metal and thick\$4 and (anneal \$3 or heat\$3) and reaction and ((work adj function) or work \$function) and (band with gap)).CLM.	US-PGPUB	OR	ON	2008/05/20 12:15
L8	0	(gate and stack and (insulat\$3 or dielectric) and silicon and metal and thick\$4 and (anneal \$3 or heat\$3) and reaction and (band with gap)).CLM.	US-PGPUB	OR	ON	2008/05/20 12:15
L9	1	(gate and (insulat\$3 or dielectric) and silicon and metal and thick\$4 and (anneal\$3 or heat\$3) and reaction and (band with gap)).CLM.	US-PGPUB	OR	ON	2008/05/20 12:24
L10	2	(gate and (insulat\$3 or dielectric) and silicon and metal and thick\$4 and reaction and (band with gap)).CLM.	US-PGPUB	OR	ON	2008/05/20 12:25
L11	153	(gate and (insulat\$3 or dielectric) and silicon and metal and thick\$4 and reaction).CLM.	US-PGPUB	OR	ON	2008/05/20 12:25
S1	1	("20060128125").PN.	US-PGPUB; USPAT	OR	OFF	2006/08/15 12:06
S2	1829	(work with function) and (CMOS or MOSFET or FET) and silicide	US-PGPUB; USPAT	OR	ON	2006/08/15 12:07
S3	778	S2 and (metal adj silicide)	US-PGPUB; USPAT	OR	ON	2006/08/15 13:41

S4	5	("4622735" "4830971" "5851891" "5937315" "6265272").PN.	USPAT	OR	ON	2006/12/06 17:38
S5	595	(CMOS or MOSFET) and (silicide adj gate)	USPAT	OR	ON	2006/12/06 17:39
S6	6	("5344793" "5780929" "6096638" "6117723" "6239006" "6303503").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/30 12:18
S7	250	(metal with silicide with gate) and ((mid\$gap) or (mid with gap))	US-PGPUB; USPAT	OR	ON	2008/01/28 11:57

5/20/08 12:28:10 PM

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